

**INTELLIGENT 256 BYTE EEPROM
WITH WRITE PROTECT FUNCTION**

Features

- Internally Organized Memory 256 x 8 (2K)
- Two-wire Serial Interface
- Bidirectional Data Transfer Protocol
- Byte Write Modes
- 8-byte Page Write Modes
- Write Protection Memory
- Self-timed Write/Erase Cycle (20 ms max)
- Endurance: 100000 Cycles
- Data Retention: 10 years
- On-chip Charge Pump for Programming
- Answer to Reset
- Chip Size 2,45 mm x 2,75 mm
- Operation Range from -40°C to +70°C

DC Characteristics

| Parametr, Units | Symbol | Min | Max | Test Condition |
|--|------------------|-----------------------|-----|---|
| Supply Voltage, V | Vcc | 4,5 | 5,5 | |
| Standby Current, μ A | I _{sb} | | 110 | V _{cc} = 5,5 V V _{ih} = 5,5 V V _{il} = 0 V |
| Input Leakage Current Low Level, μ A | I _{lil} | | -10 | V _{il} = 0 V |
| Input Leakage Current High Level, μ A (V _{pp} , SCL, RST) | I _{lih} | | 10 | V _{ih} = 5,5 V |
| Input Leakage Current High Level, μ A (TEST) | I _{lih} | | 100 | V _{ih} = 5,5 V |
| Output Leakage Current High Level, μ A | I _{loh} | | 10 | V _{oh} = 5,5 V |
| Input Low Level Voltage, V | V _{il} | | 0,8 | |
| Input High Level Voltage, V | V _{ih} | V _{cc} - 0,8 | | |
| Output Low Level Voltage, V | V _{ol} | | 0,4 | I _{ol} = 2,1 mA V _{cc} = 4,5 V |
| Clock Frequency, kHz | f _c | | 100 | |

Pin Configurations

| Pin Name | Function |
|-----------------|-------------------------|
| V _{pp} | Voltage for Programming |
| SDA | Serial Data |
| TEST | Test input |
| SCL | Serial Clock |
| RST | Reset |
| V _{cc} | Supply Voltage |
| GND | Ground |